

• General Description

The TF80N04KG combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

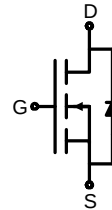
• Features

Advance high cell density Trench technology
Low $R_{DS(ON)}$ to minimize conductive loss
Low Gate Charge for fast switching
Low Thermal resistance

• Application

MB/VGA Vcore
SMPS 2nd Synchronous Rectifier
POL application
BLDC Motor driver

• Product Summary



$V_{DS} = 40V$ $I_D = 80A$
 $R_{DS(ON)}(10V \text{ typ}) = 5.1m\Omega$
 $R_{DS(ON)}(4.5V \text{ typ}) = 8.6m\Omega$



TO-251



TO-252

• Ordering Information:

Part NO.	TF80N04KG
Marking 1	80N04KG
Marking 2	TF:tuofeng; YY:year code; XX:Week; AA:device code
MOQ	TO-251:50/PCS TO-252:2500/PCS

• Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D @ T_C = 25^\circ C$	80	A
	$I_D @ T_C = 75^\circ C$	50	A
	$I_D @ T_C = 100^\circ C$	42	A
Pulsed Drain Current ①	I_{DM}	210	A
Total Power Dissipation	$P_D @ T_C = 25^\circ C$	50	W
Total Power Dissipation	$P_D @ T_A = 25^\circ C$	2.0	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;



Shenzhen Tuofeng Semiconductor Technology Co., Ltd

N-CHANNEL ENHANCEMENT MODE POWER MOSFET

SGT MOS、低内阻、低结电容开关损耗小

TF80N04KG

Single Pulse Avalanche Energy	E _{AS}	120			mJ	
Avalanche Current	I _{AS} I _{AR}	20			A	
●Thermal resistance						
Parameter	Symbol	Min.	Typ.	Max.	Unit	
Thermal resistance, junction - case	R _{thJC}	-	-	5.2	° C/W	
Thermal resistance, junction - ambient	R _{thJA}	-	-	57	° C/W	
Soldering temperature, wave soldering for 8s	T _{sold}	-	-	265	° C	
●Electronic Characteristics						
Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	40			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA	1.1	1.6	2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V			1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±20V ,V _{DS} =0V			±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A		5.1	5.9	mΩ
		V _{GS} =4.5V, I _D =20A		8.6	9.5	mΩ
Forward Transconductance	g _{FS}	V _{DS} =15V, I _D =10A		10		S
Source-drain voltage	V _{SD}	I _S =20A			1.20	V
●Electronic Characteristics						
Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iss}	V _{ds} =20V,V _{gs} =0V f = 1MHz	-	1048	-	pF
Output capacitance	C _{oss}		-	187	-	
Reverse transfer capacitance	C _{rss}		-	178	-	
●Gate Charge characteristics(T _a = 25°C)						
Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Gate Resistance	R _g	f = 1MHz		1.5		Ω
Total gate charge	Q _g	V _{DD} = 20V I _D = 20A V _{GS} = 10V	-	28	-	nC
Gate - Source charge	Q _{gs}		-	4.0	-	
Gate - Drain charge	Q _{gd}		-	6.0	-	
Turn-ON Delay time	t _{D(on)}	V _{GS} =10V ,V _{DS} =20V R _G =3.0Ω, I=20A		4.80		ns
Turn-ON Rise time	t _r			57.0		ns
Turn-Off Delay time	t _{D(off)}			17.8		ns
Turn-Off Fall time	t _f			51.0		ns

Fig.1 Power Dissipation

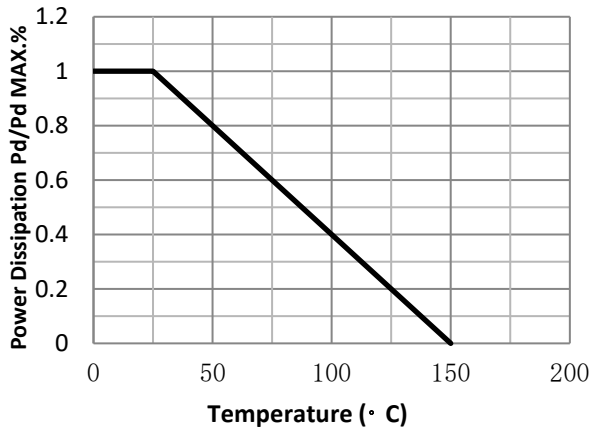


Fig.2 Typical output Characteristics

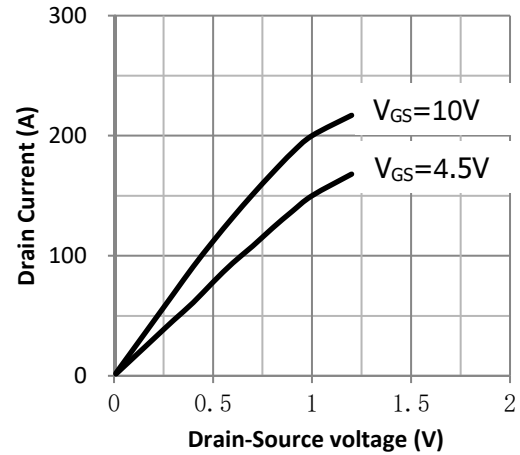


Fig.3 Threshold Voltage V.S Junction Temperature

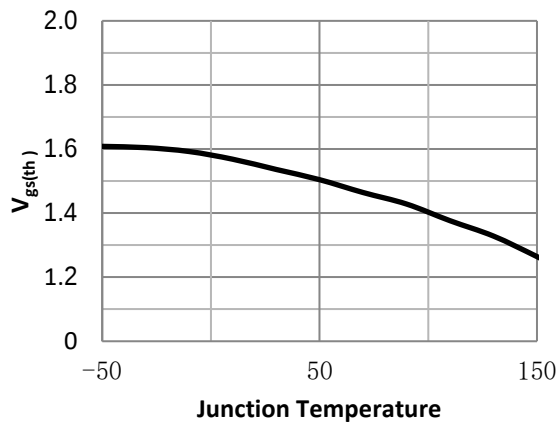


Fig.4 Resistance V.S Drain Current

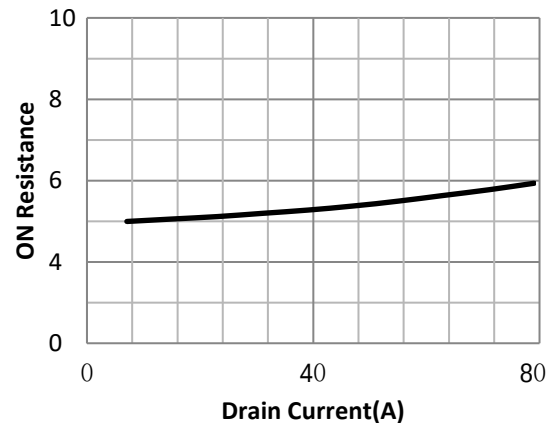


Fig.5 On-Resistance VS Drain Current

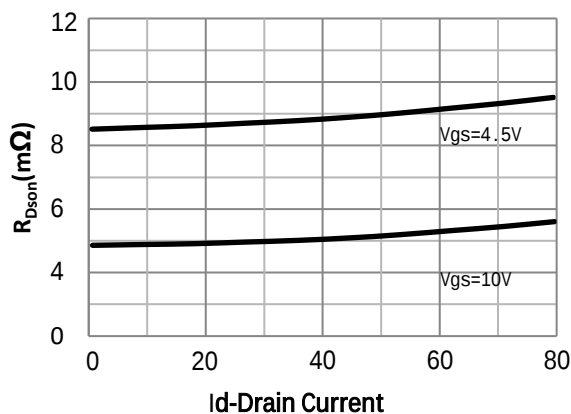


Fig.6 On-Resistance V.S Junction Temperature

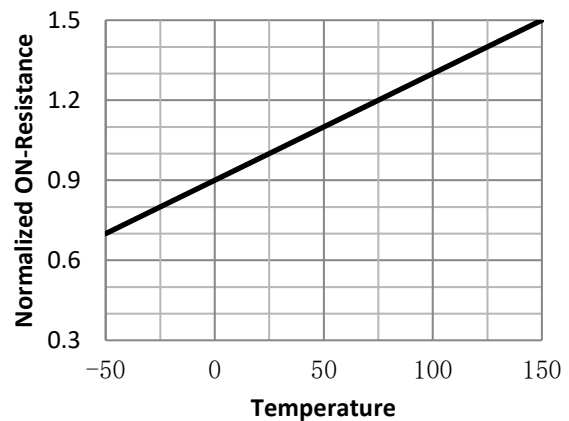


Fig.7 Switching Time Measurement Circuit

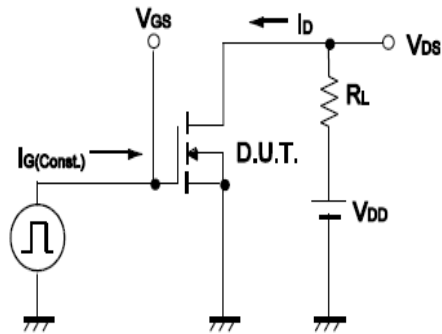


Fig.8 Gate Charge Waveform

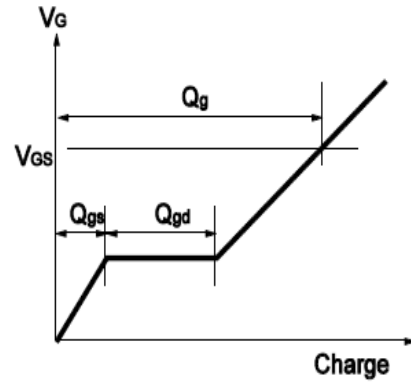


Fig.9 Switching Time Measurement Circuit

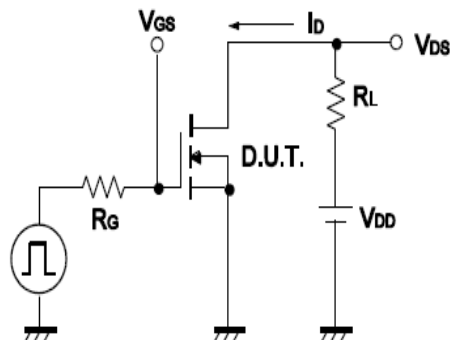


Fig.10 Gate Charge Waveform

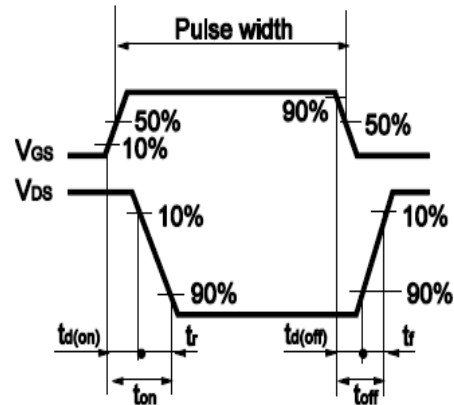


Fig.11 Avalanche Measurement Circuit

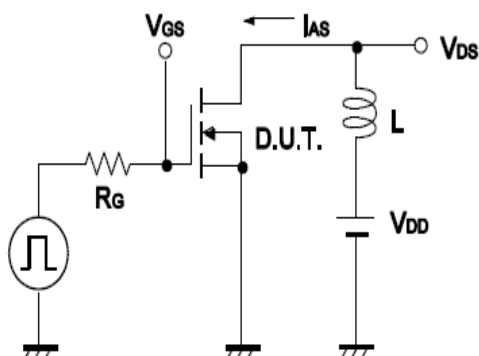
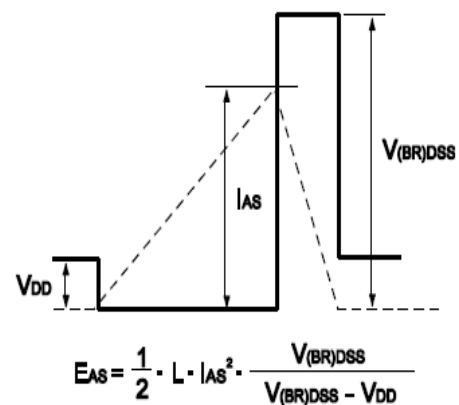
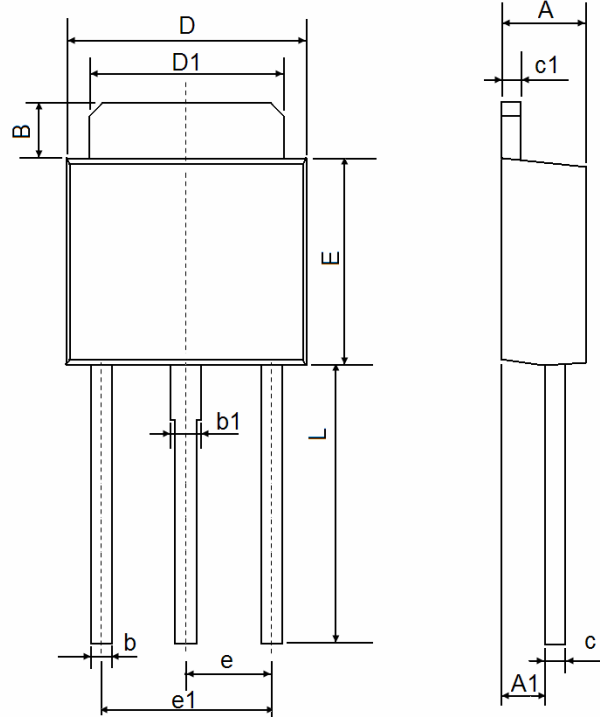


Fig.12 Avalanche Waveform



Package Information

TO-251



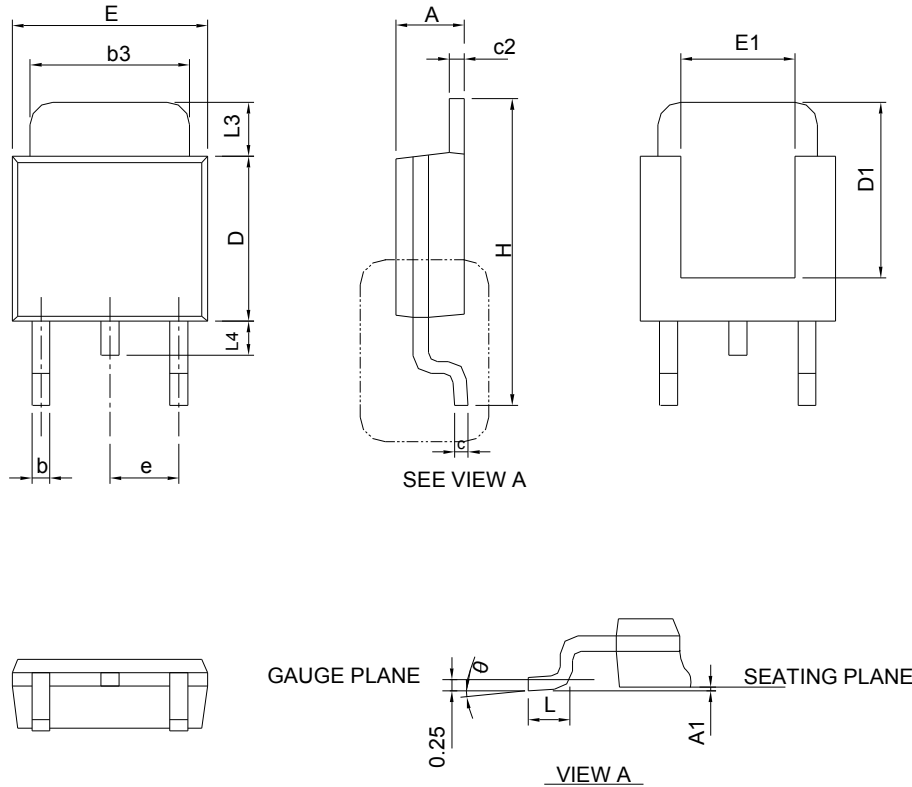
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	1.050	1.350	0.042	0.054
B	0.700	1.000	0.028	0.040
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	6.000	0.213	0.237
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	4.900	9.400	0.194	0.372

Notes

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact

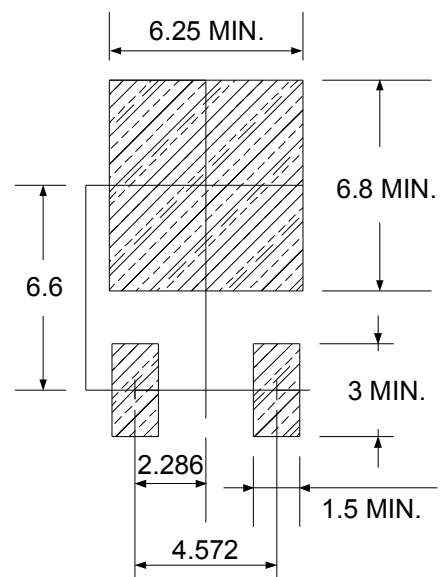
Package Information

TO-252



DIMENSIONS	TO-252			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1		0.13		0.005
b	0.50	0.89	0.020	0.035
b3	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.33	6.22	0.210	0.245
D1	4.57	6.00	0.180	0.236
E	6.35	6.73	0.250	0.265
E1	3.81	6.00	0.150	0.236
e	2.29 BSC		0.090 BSC	
H	9.40	10.41	0.370	0.410
L	0.90	1.78	0.035	0.070
L3	0.89	2.03	0.035	0.080
L4		1.02		0.040
θ	0°	8°	0°	8°

RECOMMENDED LAND PATTERN



UNIT: mm